



DMT32M4LPSW

30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	Rds(on)	I <sub>D</sub> Tc = +25°С
30V	1.7mΩ @ V <sub>GS</sub> = 10V	100A
	2.8mΩ @ V <sub>GS</sub> = 4.5V	100A

## **Description and Applications**

This new generation MOSFET is designed to minimize R<sub>DS(ON)</sub> yet maintain superior switching performance. This device is ideal for use in power managements and load switches.

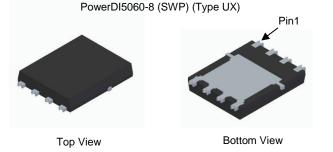
- DC-DC converters
- Load switches

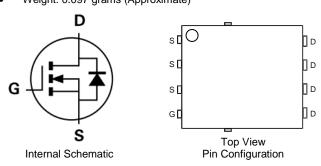
#### Features

- Thermally Efficient Package-Cooler Running Applications
- <1.1mm Package Profile Ideal for Thin Applications</p>
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

### Mechanical Data

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
  - Weight: 0.097 grams (Approximate)





# Ordering Information (Note 4)

Part Number	Bookago	Packing		
Fait Nulliber	Package	Qty.	Carrier	
DMT32M4LPSW-13	PowerDI5060-8 (SWP) (Type UX)	2500	Tape & Reel	

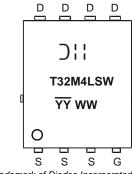
EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information

Notes:



) | | = Manufacturer's Marking <u>T32M4LSW</u> = Product Type Marking Code <u>YY</u>WW = Date Code Marking <u>YY</u> = Year (ex: 22 = 2022) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

DMT32M4LPSW Document number: DS42317 Rev. 4 - 2



## Maximum Ratings (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	ID	100 100	А		
Maximum Continuous Body Diode Forward Current (Note 6)			ls	80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	549	A		
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			lsм	549	A
Avalanche Current, L = 0.1mH			las	50	A
Avalanche Energy, L = 0.1mH			E <sub>AS</sub>	140	mJ

### Thermal Characteristics (@Tc = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	54	°C/W
Total Power Dissipation (Note 6)	$T_{\rm C} = +25^{\circ}{\rm C}$	PD	83	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

### Electrical Characteristics (@Tc = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	—	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	1	—	3	V	$V_{DS} = V_{GS}, I_D = 1mA$	
Static Drain-Source On-Resistance	Descent		1.5	1.7	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	
Static Drain-Source On-Resistance	Rds(on)	_	1.7	2.8	11122	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A	
Diode Forward Voltage	Vsd	_	0.7	1	V	$V_{GS} = 0V$ , $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 8)	•						
Input Capacitance	Ciss		3944	—		$V_{DS} = 15V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss		1267	—	pF		
Reverse Transfer Capacitance	Crss		186	—			
Gate Resistance	Rg		0.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	34	—		V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	68	—	nC		
Gate-Source Charge	Qgs	_	8	—	nc		
Gate-Drain Charge	Qgd	_	15	—			
Turn-On Delay Time	tD(ON)	_	7.2	_		$V_{DD} = 15V, V_{GS} = 10V,$ $I_D = 20A, R_G = 3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	13.2	—	ns		
Turn-Off Delay Time	tD(OFF)		37.5	—			
Turn-Off Fall Time	tF	_	23.9	—			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	28.7	—	ns		
Body Diode Reverse Recovery Charge	Qrr	_	45.8	_	nC	Is = 15A, di/dt = 500A/μs	

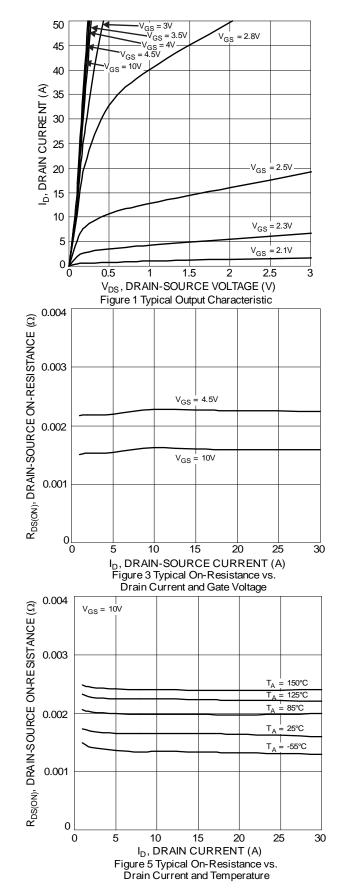
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

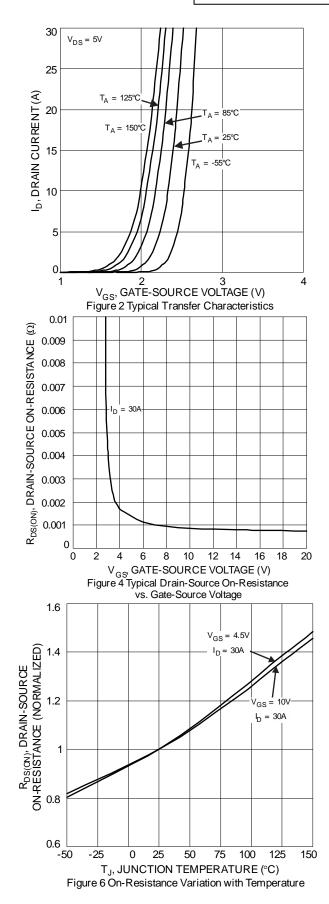
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

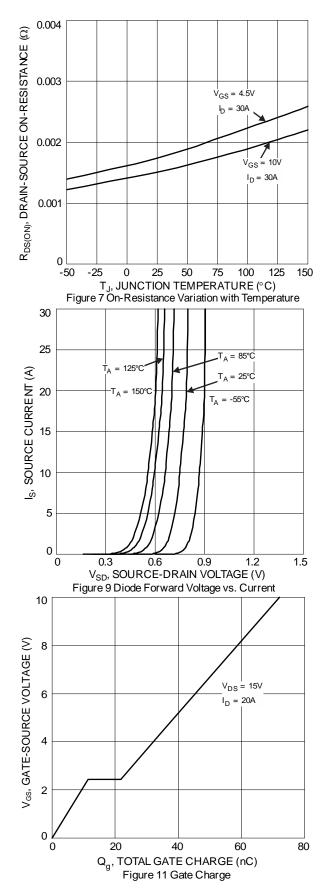


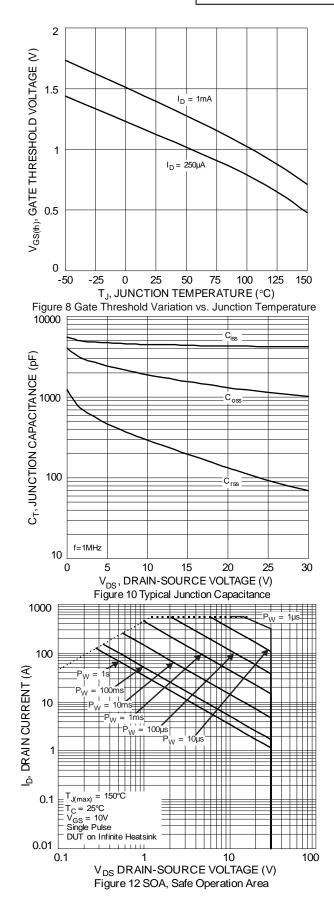




DMT32M4LPSW Document number: DS42317 Rev. 4 - 2

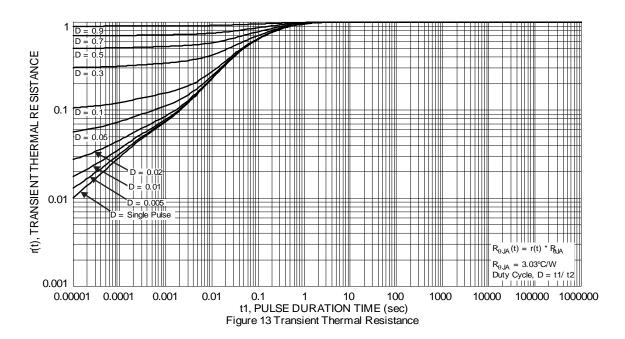








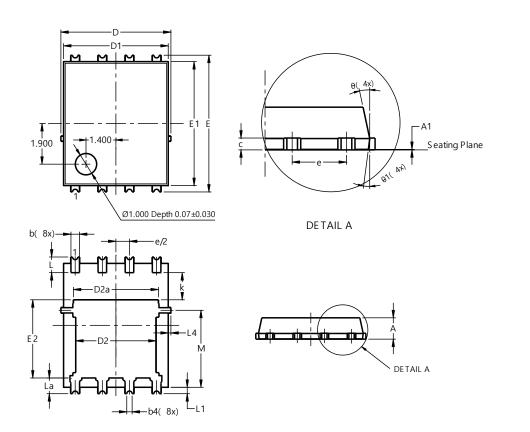






## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



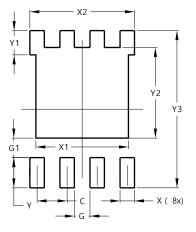
Pov	PowerDI5060-8 (SWP) (Type UX)					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05				
b	0.30	0.50	0.41			
b2	0.20	0.35	0.25			
b4	(	0.25REF				
С	0.230	0.330	0.277			
D	5	.15 BS0	2			
D1	4.70	4.70 5.10 4.9				
D2	3.56	3.96	3.76			
D2a	3.78	4.18	3.98			
E	6.40 BSC					
E1	5.60 6.00		5.80			
E2	3.46	3.86	3.66			
E2a	4.195	4.595	4.395			
е	1	1.27BSC				
k	1.05					
L	0.635	0.835	0.735			
La	0.635	0.835	0.735			
L1	0.200	0.400	0.300			
L1a	0.050REF					
L4	0.025	0.225	0.125			
М	3.205	4.005	3.605			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All	All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		

Document number: DS42317 Rev. 4 - 2



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